

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

2SK2013

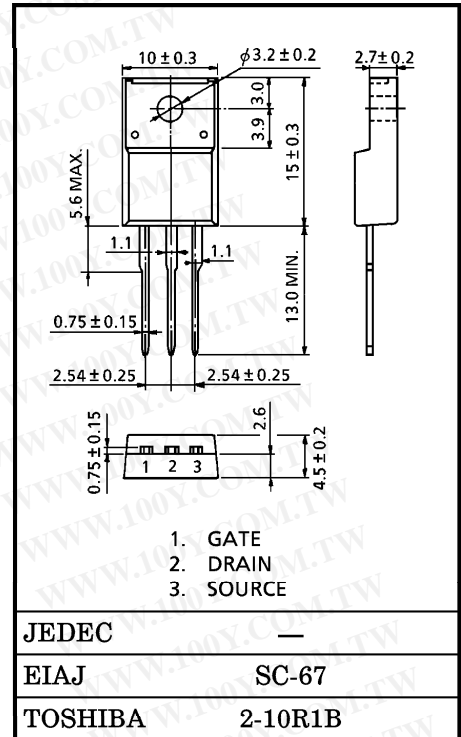
AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

Unit in mm

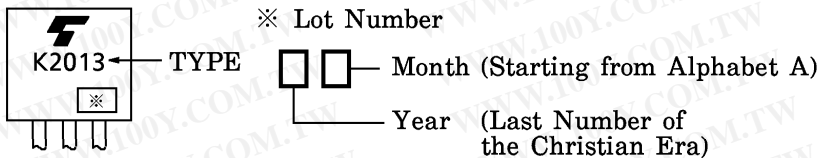
- High Breakdown Voltage : $V_{DSS}=180V$
- High Forward Transfer Admittance : $|Y_{fs}|=0.7S$ (Typ.)
- Complementary to 2SJ313

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Drain-Source Voltage	V_{DSS}	180	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	1	A
Power Dissipation ($T_c = 25^\circ C$)	P_D	25	W
Channel Temperature	T_{ch}	150	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 150$	$^\circ C$



MARKING



Weight : 1.9g

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

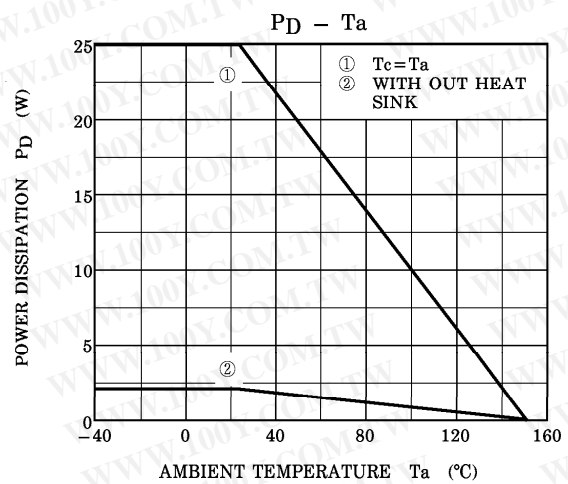
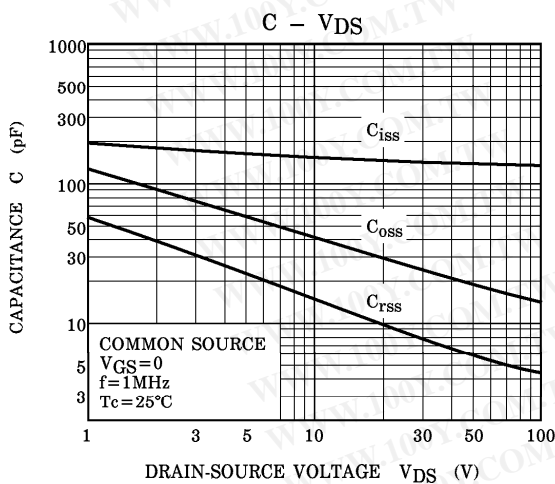
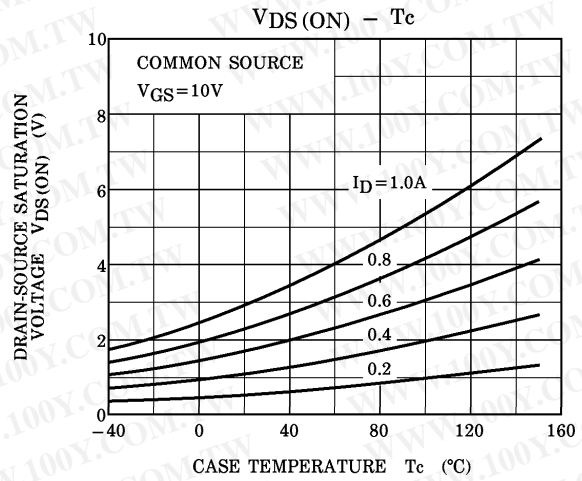
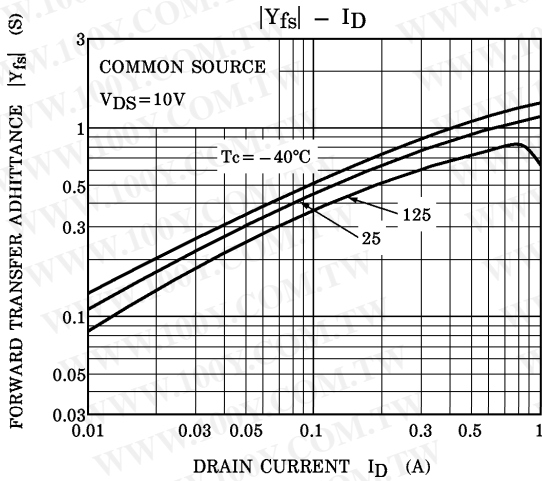
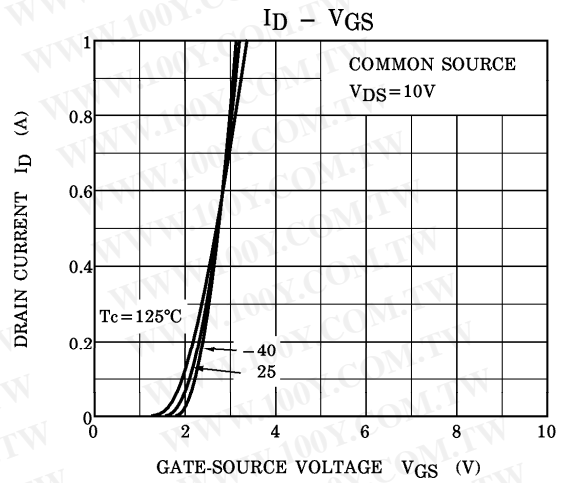
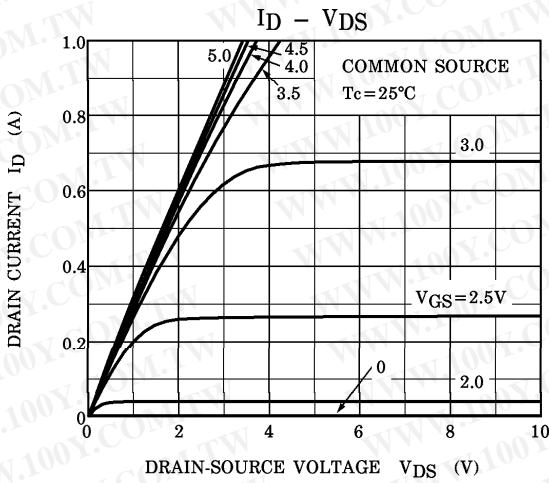
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{DS}=0, V_{GS}=\pm 20V$	—	—	± 100	nA
Drain-Source Breakdown Voltage	$V(BR)_{DSS}$	$I_D=10mA, V_{GS}=0$	180	—	—	V
Gate-Source Cut-off Current	$V_{GS(OFF)}$ (Note)	$V_{DS}=10V, I_D=10mA$	0.8	—	2.8	V
Drain-Source Saturation Voltage	$V_{DS(ON)}$	$I_D=0.6A, V_{GS}=10V$	—	1.7	3.0	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS}=10V, I_D=0.3A$	—	0.7	—	S
Input Capacitance	C_{iss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$	—	170	—	pF
Output Capacitance	C_{oss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$	—	45	—	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS}=10V, V_{GS}=0, f=1MHz$	—	17	—	pF

Note : $V_{GS(OFF)}$ Classification O : 0.8~1.6, Y : 1.4~2.8

This transistor is the electrostatic sensitive device.
 Please handle with caution.

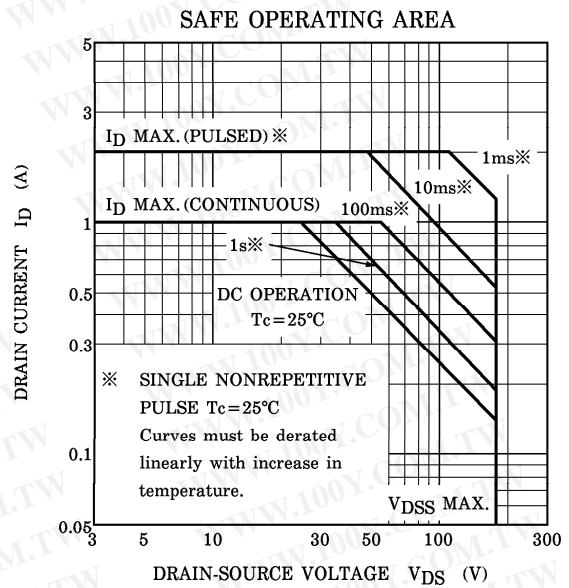
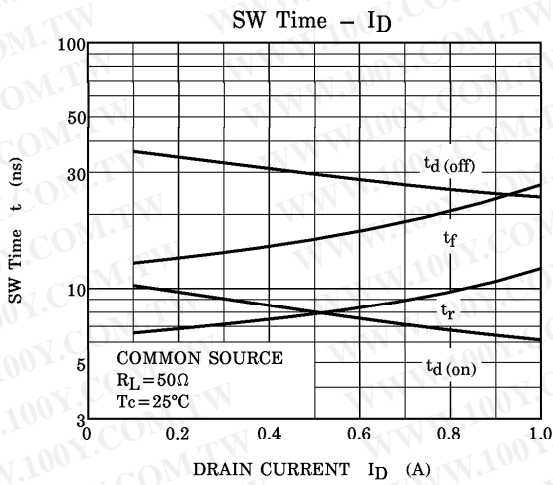
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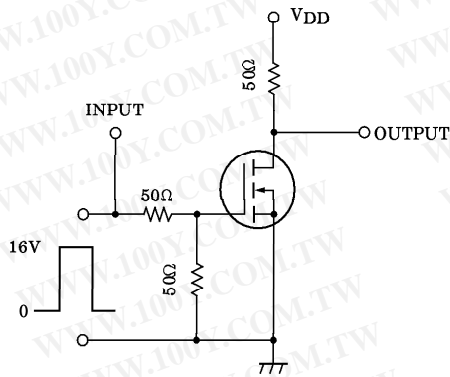


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TEST CIRCUIT



WAVEFORMS

